Noelle gogneau

List of Publications by Year
in descending order

93 papers	1,572 citations	279701 23 h-index	330025 37 g-index
95 all docs	95 docs citations	95 times ranked	2209 citing authors

#	Article	IF	Citations
1	Electromechanical conversion efficiency of GaN NWs: critical influence of the NW stiffness, the Schottky nano-contact and the surface charge effects. Nanoscale, 2022, 14, 4965-4976.	2.8	3
2	The elevated colour rendering of white-LEDs by microwave-synthesized red-emitting (Li,) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 707 Td (M Transactions, 2021, 50, 3044-3059.	1.6	16
3	Surface Microscopy of Atomic and Molecular Hydrogen from Field-Evaporating Semiconductors. Journal of Physical Chemistry C, 2021, 125, 17078-17087.	1.5	4
4	Investigation of the effect of the doping order in GaN nanowire pâ€“n junctions grown by molecular-beam epitaxy. Nanotechnology, 2021, 32, 085705.	1.3	7
5	Selective Area Growth of GaN Nanowires on Graphene Nanodots. Crystal Growth and Design, 2020, 20, 552-559.	1.4	20
6	Heat Dissipation in Flexible Nitride Nanowire Light-Emitting Diodes. Nanomaterials, 2020, 10, 2271.	1.9	3
7	A Transient Grating Method to Measure the Dispersion of Elastic Waves in Nanostructures. Journal of Physics: Conference Series, 2020, 1461, 012022.	0.3	0
8	In Situ X-ray Diffraction Study of GaN Nucleation on Transferred Graphene. Crystal Growth and Design, 2020, 20, 4013-4019.	1.4	7
9	Colour optimization of phosphor-converted flexible nitride nanowire white light emitting diodes. JPhys Photonics, 2019, 1, 035003.	2.2	9
10	1D Nanostructure-Based Piezo-Generators. Nanomaterials, 2019, 9, 1474.	1.9	2
11	GaN/Ga2O3 Core/Shell Nanowires Growth: Towards High Response Gas Sensors. Applied Sciences (Switzerland), 2019, 9, 3528.	1.3	13
12	Optical properties of GaN nanowires grown on chemical vapor deposited-graphene. Nanotechnology, 2019, 30, 214005.	1.3	11
13	Investigation of GaN nanowires containing AlN/GaN multiple quantum discs by EBIC and CL techniques. Nanotechnology, 2019, 30, 214006.	1.3	5
14	Electron beam induced current investigation of Ga(In)N nanowires (Conference Presentation). , 2019, , .		0
15	Morphology Tailoring and Growth Mechanism of Indium-Rich InGaN/GaN Axial Nanowire Heterostructures by Plasma-Assisted Molecular Beam Epitaxy. Crystal Growth and Design, 2018, 18, 2545-2554.	1.4	14
16	Evaluation of Effective Elastic Properties of Nitride NWs/Polymer Composite Materials Using Laser-Generated Surface Acoustic Waves. Applied Sciences (Switzerland), 2018, 8, 2319.	1.3	8
17	High Frequency Elastic Properties of Nitride Nanowires-Based Structures. Journal of Physics: Conference Series, 2018, 1092, 012014.	0.3	0
18	Nanogenerators based on piezoelectric GaN nanowires grown by PA-MBE and MOCVD. , 2018, , .		0

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19	Probing elastic properties of nanowire-based structures. Applied Physics Letters, 2018, 113, .	1.5	9
20	Light emission from localised point defects induced in GaN crystal by a femtosecond-pulsed laser. Optical Materials Express, 2018, 8, 2703.	1.6	17
21	Composition Metrology of Ternary Semiconductor Alloys Analyzed by Atom Probe Tomography. Journal of Physical Chemistry C, 2018, 122, 16704-16714.	1.5	22
22	High Piezoelectric Conversion Properties of Axial InGaN/GaN Nanowires. Nanomaterials, 2018, 8, 367.	1.9	14
23	Flexible optoelectronics based on nitride nanostructures (Conference Presentation). , 2018, , .		0
24	Energy harvesting efficiency in GaN nanowire-based nanogenerators: the critical influence of the Schottky nanocontact. Nanoscale, 2017, 9, 4610-4619.	2.8	29
25	Interface dipole and band bending in the hybrid <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>p</mml:mi><mml:mo>â^'</mml:mo><mml:mi>n</mml:mi heterojunction <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Mo</mml:mi><mml:msub><mml:mi mathvariant="normal">S</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:mo>/</mml:mo><mml:mi>GaN</mml:mi><mml:mrow	1.1	57
26	Physical Review B, 2017, 96, . Yellow and green luminescence in single-crystal Ge-catalyzed GaN nanowires grown by low pressure chemical vapor deposition. Optical Materials Express, 2017, 7, 1995.	1.6	12
27	High Sensitivity Piezogenerator Based on GaN Nanowires. Proceedings (mdpi), 2017, 1, 587.	0.2	0
28	Flexible Optoelectronic Devices Based on Nitride Nanowires Embedded in Polymer Films. , 2017, , .		0
29	Wavelength tunable ultrafast fiber laser via reflective mirror with taper structure. Applied Optics, 2016, 55, 10463.	2.1	1
30	Piezo-generator integrating a vertical array of GaN nanowires. Nanotechnology, 2016, 27, 325403.	1.3	50
31	Nitride Nanowires: From Rigid to Flexible Piezo-generators. Journal of Physics: Conference Series, 2016, 773, 012010.	0.3	1
32	Self-induced growth of vertical GaN nanowires on silica. Nanotechnology, 2016, 27, 135602.	1.3	33
33	Large area graphene nanomesh: an artificial platform for edge-electrochemical biosensing at the sub-attomolar level. Nanoscale, 2016, 8, 15479-15485.	2.8	28
34	Epitaxy of GaN Nanowires on Graphene. Nano Letters, 2016, 16, 4895-4902.	4.5	115
35	From single III-nitride nanowires to piezoelectric generators: New route for powering nomad electronics. Semiconductor Science and Technology, 2016, 31, 103002.	1.0	45
36	Electron beam induced current microscopy investigation of GaN nanowire arrays grown on Si substrates. Materials Science in Semiconductor Processing, 2016, 55, 72-78.	1.9	9

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37	Self-organized metal-semiconductor epitaxial graphene layer on off-axis 4H-SiC(0001). Nano Research, 2015, 8, 1026-1037.	5.8	23
38	Investigation of structural and electronic properties of epitaxial graphene on 3C–SiC(100)/Si(100) substrates. Nanotechnology, Science and Applications, 2014, 7, 85.	4.6	10
39	GaN nanowires for piezoelectric generators. Physica Status Solidi - Rapid Research Letters, 2014, 8, 414-419.	1.2	23
40	Ultra-thin engraved 3D taper structure in a crystalline material using FIB. Microelectronic Engineering, 2014, 129, 12-16.	1.1	2
41	Impact of the GaN nanowire polarity on energy harvesting. Applied Physics Letters, 2014, 104, .	1.5	20
42	From nanographene to monolayer graphene on 6H-SiC(0001) substrate. Applied Physics Letters, 2013, 102, 253108.	1.5	13
43	Control of the degree of surface graphitization on 3C-SiC(100)/Si(100). Surface Science, 2012, 606, 217-220.	0.8	19
44	N-Polar GaN Nanowires Seeded by Al Droplets on Si(111). Crystal Growth and Design, 2012, 12, 2724-2729.	1.4	54
45	Sharp interface in epitaxial graphene layers on 3<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>C</mml:mi></mml:mrow></mml:math>-SiC(100)/Si(100) wafers. Physical Review B, 2011, 83, .	1.1	45
46	Optics, morphology, and growth kinetics of GaAs/AlxGa1â^'xAs quantum wells grown on vicinal substrates by metalorganic vapor phase epitaxy. Physical Review B, 2011, 84, .	1.1	4
47	p and n-type germanium layers grown using iso-butyl germane in a III-V metal-organic vapor phase epitaxy reactor. Thin Solid Films, 2011, 519, 4186-4191.	0.8	19
48	Selective growth of site-controlled Quantum Dots. , 2011, , .		0
49	Engineering of InAsP/InP quantum dot emission for long-distance quantum communications. , 2010, , .		0
50	Development of ion sources from ionic liquids for microfabrication. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, L25-L27.	0.6	39
51	One Step Nano-Selective Area Growth of Localized InAs/InP Quantum Dots For Single Photon Source Applications. Materials Research Society Symposia Proceedings, 2009, 1228, 120701.	0.1	0
52	First results on the apollon project multi-approach for high efficiency integrated and intelligent concentrating PV modules (systems). , 2009, , .		6
53	Single photon sources using InAs/InP quantum dots. Proceedings of SPIE, 2009, , .	0.8	1
54	One-step nano-selective area growth (nano-SAG) of localized InAs/InP quantum dots: First step towards single-photon source applications. Journal of Crystal Growth, 2008, 310, 3413-3415.	0.7	9

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55	Tuning InAs/InP(001) quantum dot emission from 1.55 to 2 Î¼m by varying cap-layer growth rate in metalorganic vapor phase epitaxy. , 2008, , .		0
56	One step Nano Selective Area Growth of localized InAs/InP quantum dots for single photon source applications. , 2008, , .		0
57	InAsP/InP(001) quantum dots emitting at 1.55 Î¼m grown by metalorganic vapor phase epitaxy. , 2008, , .		0
58	Time-resolved characterization of InAsPâˆ•InP quantum dots emitting in the C-band telecommunication window. Applied Physics Letters, 2008, 93, 073106.	1.5	17
59	Metal organic vapor phase epitaxy of InAsP/InP(001) quantum dots for 1.55Î¼m applications: Growth, structural, and optical properties. Journal of Applied Physics, 2008, 104, 043504.	1.1	27
60	Density of InAsâˆ•InP(001) quantum dots grown by metal-organic vapor phase epitaxy: Independent effects of InAs and cap-layer growth rates. Applied Physics Letters, 2007, 91, .	1.5	14
61	Raman study and theoretical calculations of strain in GaN quantum dot multilayers. Physical Review B, 2006, 73, .	1.1	15
62	Resonant Raman scattering in self-assembledGaNâˆ•AlNquantum dots. Physical Review B, 2006, 74, .	1.1	21
63	Step ordering induced by nonplanar patterning of GaAs surfaces. Applied Physics Letters, 2006, 88, 203104.	1.5	6
64	Correlation between optical properties and interface morphology of GaAsâˆ•AlGaAs quantum wells. Applied Physics Letters, 2006, 88, 141917.	1.5	15
65	Influence of stacking on optical characteristics of GaN/AlN self-organized quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2056-2059.	0.8	2
66	Comparison of the structural quality in Ga-face and N-face polarity GaN/AlN multiple-quantum-well structures. Semiconductor Science and Technology, 2006, 21, 612-618.	1.0	33
67	Sub-meV photoluminescence linewidth and >106cm2âˆ•Vs electron mobility in AlGaAsâˆ•GaAs quantum wells grown by metalorganic vapor phase epitaxy on slightly misoriented substrates. Journal of Applied Physics, 2006, 99, 093515.	1.1	30
68	Raman study of strain in GaN/AlN quantum dot multilayered structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2328-2331.	0.8	3
69	Raman Study of Strain Relaxation in GaN/AlN Quantum Dots. AIP Conference Proceedings, 2005, , .	0.3	0
70	Surfactant effect of gallium during the growth of GaN on AlN(0001Â¯) by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2004, 85, 1421-1423.	1.5	24
71	Photoluminescence of GaN/AlN Quantum Dots Grown on SiC Substrates. Materials Science Forum, 2004, 457-460, 1593-1596.	0.3	0
72	Control of the 2D/3D Transition of Cubic GaN/AlN Nanostructures on 3C-SiC Epilayers. Materials Science Forum, 2004, 457-460, 1561-1564.	0.3	1

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73	Growth of GaN/AlN Quantum Dots on SiC (000-1) by Plasma-Assisted MBE. Materials Science Forum, 2004, 457-460, 1557-1560.	0.3	0
74	Direct Growth of High Quality GaN by Plasma Assisted Molecular Beam Epitaxy on 4H-SiC Substrates. Materials Science Forum, 2004, 457-460, 1577-1580.	0.3	2
75	Growth of N-Face Polarity III-Nitride Heterostructures on C-Face 4H-SiC by Plasma-Assisted MBE. Materials Science Forum, 2004, 457-460, 1573-1576.	0.3	0
76	Recent progress in growth and physics of GaN/AlN quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 1445-1450.	0.8	12
77	Properties of self-assembled Ga-polar and N-polar GaN/AlN quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2504-2507.	0.8	2
78	GaN quantum dots by molecular beam epitaxy. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 540-545.	1.3	9
79	Influence of AlN overgrowth on structural properties of GaN quantum wells and quantum dots grown by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 2004, 96, 1104-1110.	1.1	57
80	Growth kinetics of N-face polarity GaN by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2004, 84, 3684-3686.	1.5	65
81	Effects of stacking on the structural and optical properties of self-organized GaN/AlN quantum dots. Applied Physics Letters, 2004, 84, 4224-4226.	1.5	30
82	Comprehensive overview on elastic strain relaxation mechanisms in nitride heterostructures: Stranskiâ€“Krastanow versus Frankâ€“Van der Merwe growth mode. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2525-2528.	0.8	3
83	Molecular-beam epitaxial growth and characterization of quaternary IIIâ€“nitride compounds. Journal of Applied Physics, 2003, 94, 3121-3127.	1.1	60
84	Surfactant effect of In for AlGaN growth by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 2003, 93, 1550-1556.	1.1	77
85	Structure of GaN quantum dots grown under â€œmodified Stranskiâ€“Krastanowâ€•conditions on AlN. Journal of Applied Physics, 2003, 94, 2254-2261.	1.1	102
86	In incorporation during the growth of quaternary III-nitride compounds by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2003, 82, 2242-2244.	1.5	31
87	Growth of Quaternary AlInGaN/GaN Heterostructures by Plasma Assisted MBE. Materials Research Society Symposia Proceedings, 2002, 743, L4.5.1.	0.1	0
88	In as a Surfactant for the Growth of AlGaN/GaN Heterostructures by Plasma Assisted MBE. Materials Research Society Symposia Proceedings, 2002, 743, L6.1.1.	0.1	0
89	Formation of quantum dots by self-rearrangement of metastable 2D GaN. Materials Research Society Symposia Proceedings, 2002, 743, L8.8.1.	0.1	0
90	GaN islanding by spontaneous rearrangement of a strained two-dimensional layer on (0001) AlN. Applied Physics Letters, 2002, 81, 3064-3066.	1.5	55

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91	Assessment of AlGaN Growth by Plasma Assisted MBE Using In as a Surfactant. Physica Status Solidi (B): Basic Research, 2002, 234, 726-729.	0.7	7
92	Controlling the Morphology of GaN Layers Grown on AlN in Ga Self-Surfactant Conditions: from Quantum Wells to Quantum Dots. Physica Status Solidi (B): Basic Research, 2002, 234, 931-934.	0.7	0
93	Investigating the secondary electron emission of nanomaterials induced by a high resolution proton beam. Physica Status Solidi (B): Basic Research, 0, , .	0.7	0